

CDBJFSC10650-G

Reverse Voltage: 650 V

Forward Current: 10 A

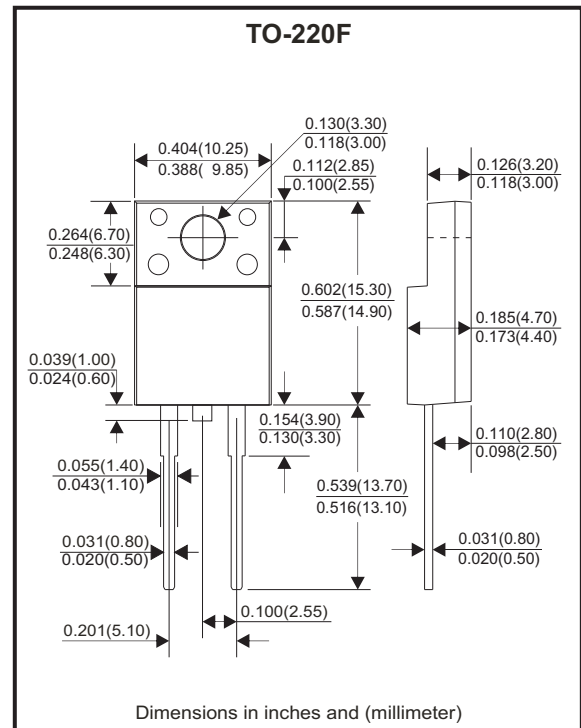
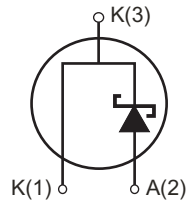
RoHS Device



Features

- Rated to 650V at 10 Amps
- Short recovery time.
- High speed switching possible.
- High frequency operation.
- High temperature operation.
- Temperature independent switching behaviour.
- Positive temperature coefficient on VF.

Circuit diagram



Maximum Rating (at T_A=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Value	Unit
Repetitive peak reverse voltage		V _{RRM}	650	V
Surge peak reverse voltage		V _{RSM}	650	V
DC blocking voltage		V _{DC}	650	V
Typical continuous forward current	T _C = 120°C		10	A
Repetitive peak forward surge current	T _C = 25°C, t _p = 10ms Half sine wave, D = 0.3	I _{FRM}	50	A
Non-repetitive peak forward surge current	T _C = 25°C, t _p = 10ms Half sine wave	I _{FSM}	100	A
Power dissipation	T _C = 25°C	P _{TOT}	39.4	W
	T _C = 110°C		17.1	
Typical thermal resistance	Junction to case	R _{θJC}	3.81	°C/W
Operating junction temperature range		T _J	-55 ~ +175	°C
Storage temperature range		T _{STG}	-55 ~ +175	°C

Electrical Characteristics (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Typ	Max	Unit
Forward voltage	$I_F = 10\text{ A}$, $T_J = 25^\circ\text{C}$	V_F	1.48	1.7	V
	$I_F = 10\text{ A}$, $T_J = 175^\circ\text{C}$		1.7		
Reverse current	$V_R = 650\text{ V}$, $T_J = 25^\circ\text{C}$	I_R	20	100	μA
	$V_R = 650\text{ V}$, $T_J = 175^\circ\text{C}$		30		
Total capacitive charge	$V_R = 400\text{ V}$, $T_J = 150^\circ\text{C}$ $Q_C = \int_0^{V_R} C(V) dv$	Q_C	36		nC
Total capacitance	$V_R = 0\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$	C	710		pF
	$V_R = 200\text{ V}$, $T_J = 25^\circ\text{C}$, $f = 1\text{ MHz}$		72		

Typical Characteristics (CDBJFSC10650-G)

Fig.1 - Forward Characteristics

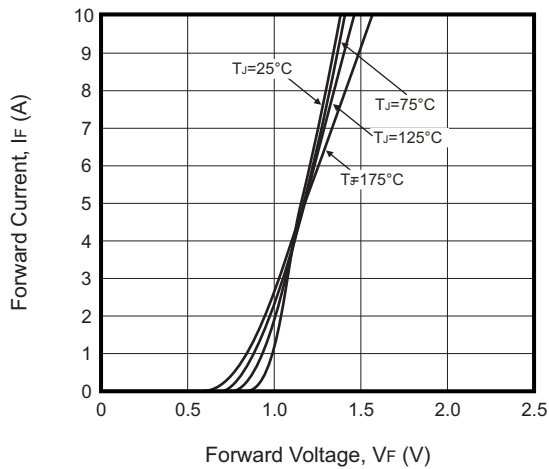


Fig.2 - Reverse Characteristics

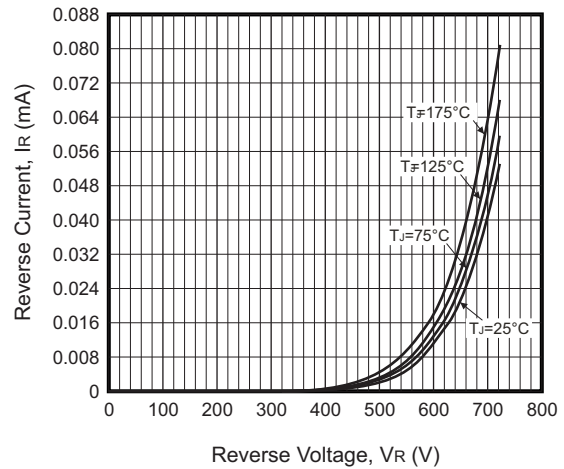


Fig.3 - Current Derating

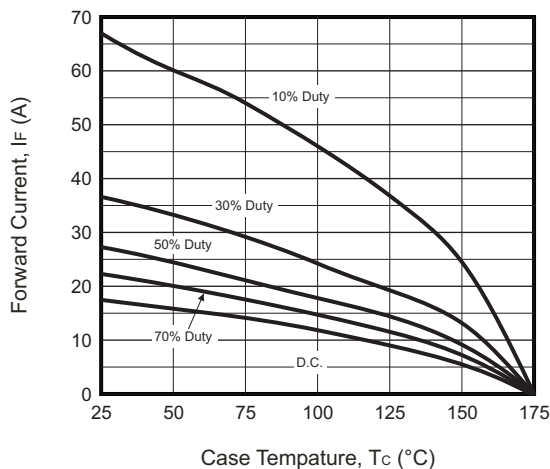


Fig.4 - Capacitance vs. Reverse Voltage

